

10/511558

DT04 Rec'd PCT/PTO 15 OCT 2004

LISTING OF CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently amended) A process for producing copy protection for an electronic circuit, comprising the steps of:
providing a substrate ~~(1)~~ ~~which has~~ having semiconductor structures ~~(2)~~ on at least a first side ~~(1a)~~ of the substrate ~~(1)~~;

providing a material for coating the substrate ~~(1)~~; and
coating the substrate ~~(1)~~ with a copy-protect layer ~~(4)~~,
~~which is applied~~ by evaporation coating.

2. (Currently amended) The process as claimed in claim 1, wherein the semiconductor structures ~~(2)~~, at least in regions, are covered by ~~means of~~ the copy-protect layer ~~(4)~~, the copy-protect layer ~~(4)~~ being matched to the substrate ~~(1)~~ ~~in such a way so~~ that an etching process ~~which~~ that dissolves the copy-protect layer ~~(4)~~ likewise attacks the substrate ~~(1)~~ ~~in such a manner so~~ that the semiconductor structures ~~(2)~~ are at least partially destroyed.

3. (Currently amended) The process as claimed in claim 1 ~~or~~ 2, wherein the substrate ~~(1)~~ comprises a semiconductor layer of silicon[[,]] and the copy-protect layer ~~(4)~~ ~~contains~~ comprises silicon.

4. (Currently amended) The process as claimed in ~~one of the preceding claims~~ claim 1, wherein ~~a continuous layer is applied as~~ the copy-protect layer ~~(4)~~ is a continuous layer.

5. (Currently amended) The process as claimed in ~~one of the preceding claims~~ claim 1, wherein the copy-protect layer (4) comprises ~~glass, in particular~~ silicate glass.

6. (Currently amended) The process as claimed in ~~one of the preceding claims~~ claim 1, wherein the copy-protect layer (4) comprises a borosilicate glass with aluminum oxide and alkali metal oxide fractions.

7. (Currently amended) The process as claimed in ~~one of the preceding claims~~ claim 1, wherein the copy-protect layer (4) comprises ~~an at least~~ a binary system.

8. (Currently amended) The process as claimed in ~~one of the preceding claims~~ claim 1, wherein the copy-protect layer (4) comprises a shield against electromagnetic waves.

9. (Currently amended) The process as claimed in ~~one of the preceding claims~~ claim 1, wherein coating the substrate with the copy-protect layer (4) ~~is applied by~~ comprises evaporation coating induced by thermal evaporation or by electron beam evaporation.

10. (Currently amended) The process as claimed in ~~one of the preceding claims~~ claim 1, wherein the copy-protect layer (4) is applied to the substrate in a thickness of from 0.01 to 1000 μm .

11. (Currently amended) The process as claimed in ~~one of the preceding claims~~ claim 1, wherein ~~the~~ coating of the substrate ~~(1)~~ with the copy-protect layer ~~(4)~~ is carried out comprises coating at a bias temperature of below 300°C.

12. (Currently amended) The process as claimed in ~~one of the preceding claims~~ claim 1, wherein ~~the~~ coating of the substrate ~~(1)~~ with the copy-protect layer ~~(4)~~ is carried out comprises coating at a pressure of from 10^{-3} mbar to 10^{-7} mbar.

13. (Currently amended) The process as claimed in ~~one of the preceding claims~~, wherein claim 1, further comprising applying a glass layer ~~(14)~~ is applied to a second side ~~(1b)~~ of the substrate ~~(1)~~, ~~which~~ wherein the second side is on the opposite side from the first side ~~(1a)~~.

14. (Currently amended) The process as claimed in ~~one of the preceding claims~~, wherein claim 1, further comprising applying a plastics layer ~~(5)~~ is applied to a second side ~~(1b)~~ of the substrate ~~(1)~~, ~~which~~ wherein the second side is on the opposite side from the first side ~~(1a)~~.

15. (Currently amended) The process as claimed in ~~one of the preceding claims, wherein~~ claim 1, further comprising:

thinning the substrate (1) is thinned;

producing etching pits (6) with connection structure regions (3) ~~as etching stop are produced~~ on the first side (1a) of the substrate (1);

applying a plastics layer (10) ~~is applied~~ to a second side (1b) of the substrate (1), ~~which~~ wherein the second side is on the opposite side from the first side (1a), ~~by means of plastics lithography, with,~~ the plastics layer being applied so that the connection structure regions (3) remaining remain open;

producing contacts (7) ~~are produced~~ on the second side (1b) by coating with a conductive layer;

applying a ball grid array (8) ~~is applied;~~ and

dicing the substrate (1) ~~is diced~~ into individual chips.

16. (Currently amended) The process as claimed in claim 15, ~~wherein~~ further comprising removing the plastics layer (10) on from the second side (1b) ~~is removed again.~~

17. (Currently amended) The process as claimed in claim 1, further comprising:

~~one of the preceding claims, wherein~~ evaporation coating a second side (1b) of the substrate (1), ~~which is on the opposite side from the first side (1a), is evaporation-coated~~ with a glass layer (11) that is from 0.01 μm to 50 μm thick; and

uncovering connection structure regions (7) located beneath the glass layer (11) ~~are uncovered by means of grinding or etching.~~

18. (Currently amended) The process as claimed in ~~one of the preceding claims,~~ wherein claim 15, further comprising filling the etching pits ~~(6) are filled~~ with conductive material.

19. (Currently amended) The process as claimed in ~~one of the preceding claims,~~ wherein ~~the substrate (1) comprises~~ claim 1, further comprising:

coating the connection structures ~~which are coated with a structured covering layer (15) before the coating with the copy-protect layer (4) is carried out,~~;

thinning the copy-protect layer ~~(4) is thinned,~~ at least until the structured covering layer ~~(15)~~ has been uncovered,;

removing the structured covering layer ~~(15) is removed in order to uncover the connection structure~~ regions ~~(3).~~

20. (Currently amended) The process as claimed in ~~one of the preceding claims~~ claim 19, wherein at least sections of a the structured covering layer ~~(15)~~ and at least sections of the copy-protect layer ~~(4)~~ are removed by ~~means of~~ a lift-off technique.

21. (Currently amended) The process as claimed in ~~one of the preceding claims,~~ wherein claim 15, further comprising applying a ball grid array ~~(18) is applied~~ to the first side ~~(1a) of the substrate (1) on the~~ connection structures ~~(3)~~ regions.

22. (Currently amended) The process as claimed in ~~one of the preceding claims~~ claim 1, wherein the semiconductor structures ~~(2)~~ comprise electronic decryption ~~means~~ devices.

23. (Cancelled)

24. (Currently amended) The electronic component with copy protection, comprising:

an electronic circuit on a substrate ~~(1) with semiconductor structures (2) on~~ having a first side ~~(1a) of the substrate (1),~~;

semiconductor structures on the first side; and

a copy-protect layer ~~(4)~~ fixedly joined to at least a region of the semiconductor structures.

25. (Currently amended) The electronic component as claimed in claim ~~23 or~~ 24, wherein the copy-protect layer ~~(4) contains~~ comprises a first material, ~~the semiconductor structures (2) being covered by the copy-protect layer (4) at least in regions, the copy-protect layer (4) being fixedly joined to the substrate (1), and the first material being determined in such a manner that~~ being selected so that an etching process ~~which~~ that dissolves the copy-protect layer ~~likewise attacks the substrate in such a manner that the also destroys~~ a portion of the electronic circuit ~~is destroyed.~~

26. (Currently amended) The electronic component as claimed in ~~one of claims 23 to~~ claim 25, wherein the substrate ~~(1) comprises a semiconductor layer of silicon and the copy-protect layer (4) contains~~ comprises silicon.

27. (Currently amended) The electronic component as claimed in ~~one of claims 23 to 26~~ claim 24, wherein the copy-protect layer ~~(4) comprises~~ is a continuous layer.

28. (Currently amended) The electronic component as claimed in ~~one of claims 23 to 27~~ claim 24, wherein the copy-protect layer ~~(4)~~ comprises ~~glass, in particular~~ silicate glass.

29. (Currently amended) The electronic component as claimed in ~~one of claims 23 to 28~~ claim 24, wherein the copy-protect layer ~~(4)~~ comprises a borosilicate glass with aluminum oxide and alkali metal oxide fractions.

30. (Currently amended) The electronic component as claimed in ~~one of claims 23 to 29~~ claim 24, wherein the copy-protect layer ~~(4)~~ is ~~applied by~~ an evaporation coating.

31. (Currently amended) The electronic component as claimed in ~~one of claims 23 to 30~~ claim 24, wherein the copy-protect layer ~~(4)~~ comprises a binary system.

32. (Currently amended) The electronic component as claimed in ~~one of claims 23 to 31~~ claim 24, wherein the copy-protect layer ~~(4)~~ ~~comprises shielding against~~ shields electromagnetic waves.

33. (Currently amended) The electronic component as claimed in one of claims ~~23 to 32~~ claim 24, wherein the copy-protect layer ~~(4)~~ is ~~applied by evaporation coating induced by a~~ thermal evaporation coating or ~~by~~ an electron-beam evaporation coating.

34. (Currently amended) The electronic component as claimed in ~~one of claims 23 to 33~~ claim 24, wherein the copy-protect layer ~~(4)~~ is from 0.01 μm to 1000 μm thick.

35. (Currently amended) The electronic component as claimed in ~~one of claims 23 to 34, wherein the substrate (1) has~~ claim 24, further comprising connection structures ~~(3),~~ and elevated connection structures ~~(8) are~~ arranged on a second side ~~(1b) of the substrate (1), which is the second side being on the~~ opposite side from the first side ~~(1a), wherein the elevated~~ connection ~~contacts (8) being~~ structures are electrically connected to the connection structures ~~(3).~~

36. (Currently amended) The electronic component as claimed in claim 35, wherein the second side ~~(1b) of the substrate (1)~~ is coated with plastic ~~(10)~~ between the elevated connection contacts (8), with structures so that the elevated connection contacts (8) remaining structures remain uncovered ~~in such a manner that they can be contact-connected.~~

37. (Currently amended) The electronic component as claimed in claim 35 ~~or 36~~, wherein the second side ~~(1b) of the substrate (1)~~ is coated with glass ~~(11)~~ between the elevated connection contacts (8), with structures so that the elevated connection contacts (8) remaining structures remain uncovered ~~such that they can be contact-connected.~~

38. (Currently amended) The electronic component as claimed in ~~one of claims 23 to 37, wherein the substrate (1) has~~ claim 24, further comprising connection structures and elevated connection contacts ~~(18) are~~ arranged on the first side ~~(1a) of the substrate (1), the elevated connection contacts (18) being~~ electrically connected to the connection structures ~~(3).~~

39. (Currently amended) The electronic component as claimed in ~~one of claims 23 to~~ claim 38, wherein the copy-protect layer ~~(4)~~ on the first side ~~(1a)~~ of the substrate ~~(1)~~ extends between the elevated connection contacts and the connection structures (3, 18) so that the elevated connection contacts and the connection structures, ~~the connection contacts (3, 18) remaining~~ remain uncovered ~~such that they can be contact-connected.~~

40. (Currently amended) The electronic component as claimed in ~~one of claims 23 to 39,~~ wherein the electronic ~~circuit comprises~~ claim 24, further comprising a decryption means device.

41. (Currently amended) The electronic component as claimed in ~~one of claims 23 to 40~~ claim 24, wherein the copy-protect layer ~~(4)~~ has a first portion ~~(4a)~~ and a second portion ~~(4b)~~ which that ~~have different etching properties, in particular comprise materials with~~ different etching rates.

42. (Currently amended) A decryption device for decrypting encrypted signals, ~~in particular used in pay broadcasting,~~ comprising:

an electronic circuit on a substrate having a first side;
semiconductor structures on the first side;
a copy-protect layer fixedly joined to at least a region of the semiconductor structures; and
a decryption device ~~the component as claimed in one of claims 24 to 41.~~

43 through 45. (Cancelled)